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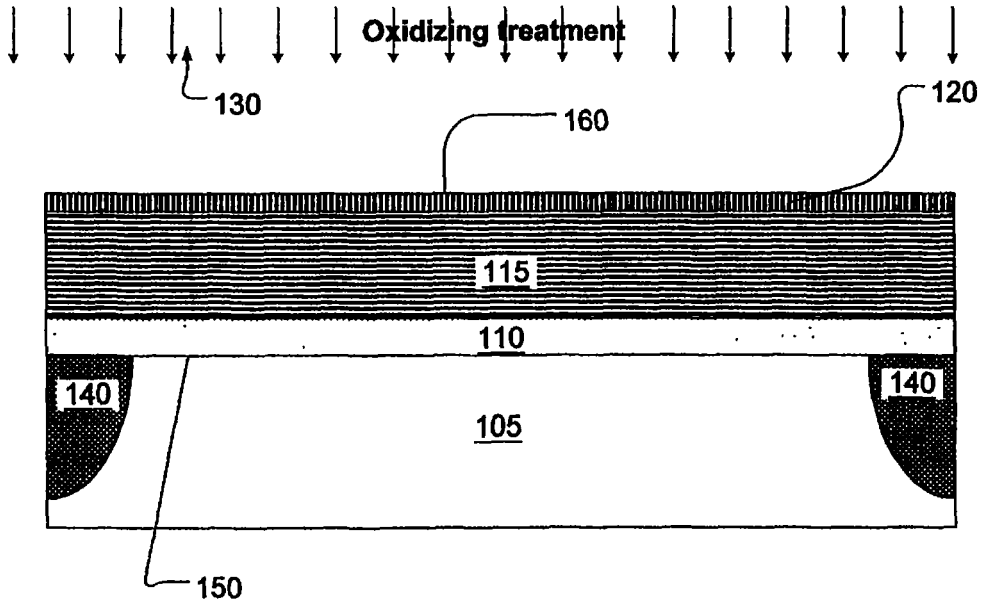
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(54) Title: BOTTOM ANTI-REFLECTIVE COATING USING RAPID THERMAL ANNEAL WITH OXIDIZING GAS



(57) Abstract: A method is provided, the method including forming a gate dielectric layer (110, 410) above a substrate layer (105) and forming a gate conductor layer (115, 415) above the gate dielectric layer (110, 410). The method also comprises forming an inorganic bottom anti-reflective coating layer (120) above the gate conductor layer (115, 415) and treating the inorganic bottom anti-reflective coating layer (120) with an oxidizing treatment (130) during a rapid thermal anneal process.

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